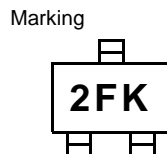
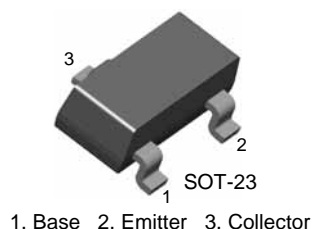


# MMBT2907AK

## PNP Epitaxial Silicon Transistor

### General Purpose Transistor



### Absolute Maximum Ratings $T_a = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	-60	V
$V_{CEO}$	Collector-Emitter Voltage	-60	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current	-600	mA
$P_C$	Collector Power Dissipation	350	mW
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	-55 ~ 150	$^\circ\text{C}$

### Electrical Characteristics $T_a = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
$BV_{CBO}$	Collector-Base Breakdown Voltage	$I_C = -10\mu\text{A}, I_E = 0$	-60		V
$BV_{CEO}$	Collector-Emitter Breakdown Voltage *	$I_C = -10\text{mA}, I_B = 0$	-60		V
$BV_{EBO}$	Emitter-Base Breakdown Voltage	$I_E = -10\mu\text{A}, I_C = 0$	-5		V
$I_{CBO}$	Collector Cut-off Current	$V_{CB} = -50\text{V}, I_E = 0$		-0.01	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$V_{CE} = -10\text{V}, I_C = -0.1\text{mA}$ $V_{CE} = -10\text{V}, I_C = -1.0\text{mA}$ $V_{CE} = -10\text{V}, I_C = -10\text{mA}$ $V_{CE} = -10\text{V}, I_C = -150\text{mA}^*$ $V_{CE} = -10\text{V}, I_C = -500\text{mA}^*$	75 100 100 100 50	300	
$V_{CE}(\text{sat})$	Collector-Emitter Saturation Voltage *	$I_C = -150\text{mA}, I_B = -15\text{mA}$ $I_C = -500\text{mA}, I_B = -50\text{mA}$		-0.4 -1.6	V V
$V_{BE}(\text{sat})$	Base-Emitter Saturation Voltage *	$I_C = -150\text{mA}, I_B = -15\text{mA}$ $I_C = -500\text{mA}, I_B = -50\text{mA}$		-1.3 -2.6	V V
$f_T$	Current Gain Bandwidth Product	$I_C = -50\text{mA}, V_{CE} = -20\text{V}, f = 100\text{MHz}$	200		MHz
$C_{ob}$	Output Capacitance	$V_{CB} = -10\text{V}, I_E = 0, f = 1.0\text{MHz}$		8	pF
$t_{ON}$	Turn On Time	$V_{CC} = -30\text{V}, I_C = -150\text{mA}$ $I_{B1} = -15\text{mA}$		50	ns
$t_{OFF}$	Turn Off Time	$V_{CC} = -6\text{V}, I_C = -150\text{mA}$ $I_{B1} = I_{B2} = -15\text{mA}$		110	ns

\* Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$

## Typical Performance Characteristics

Figure 1. DC current Gain

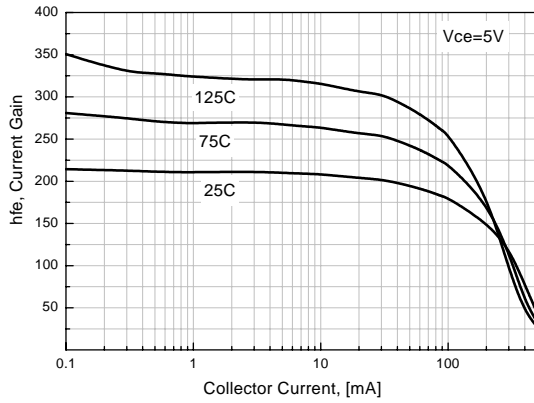


Figure 2. Collector-Emitter Saturation Voltage

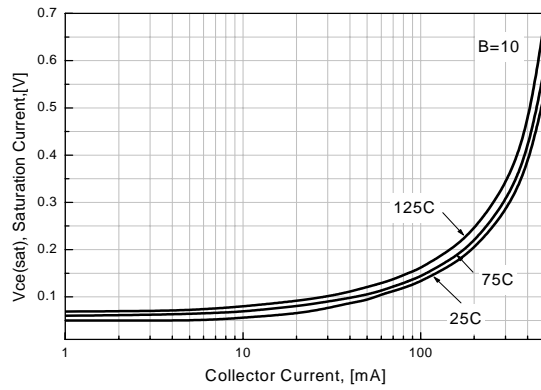


Figure 3. Base-Emitter Saturation Voltage

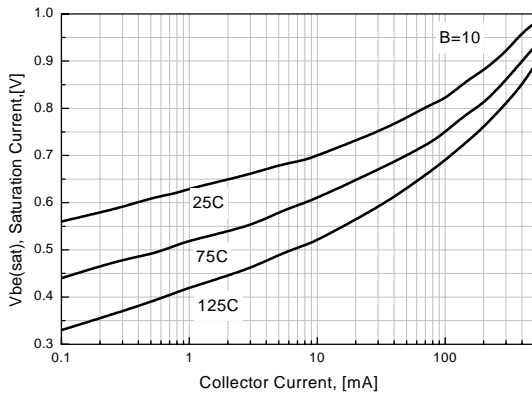


Figure 4. Collector - Base Leakage Current

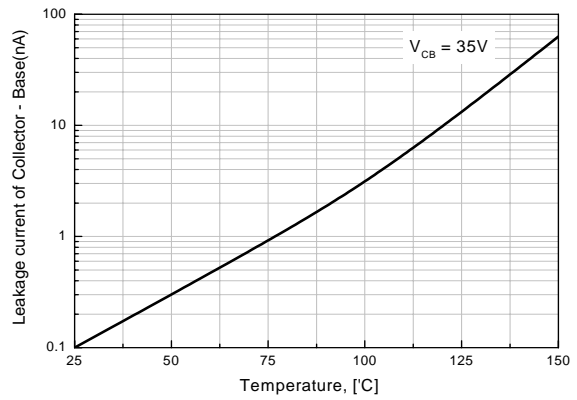


Figure 5. Output Capacitance

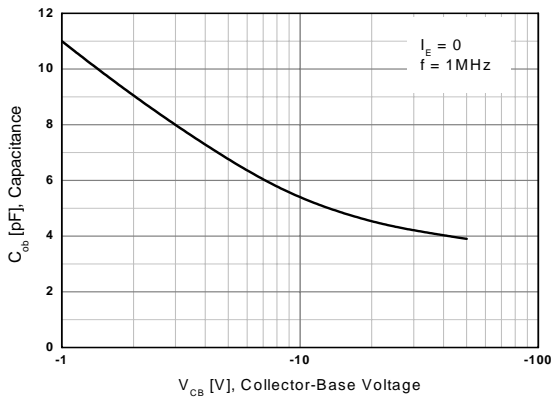
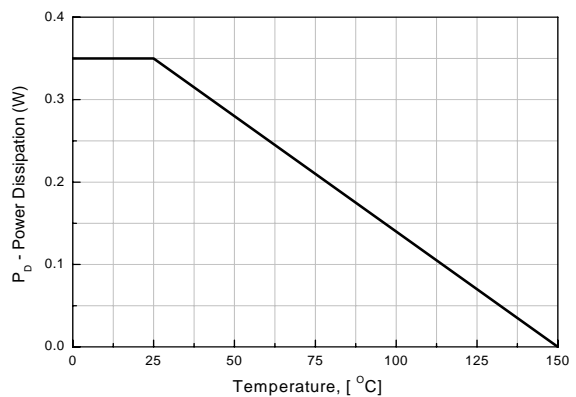
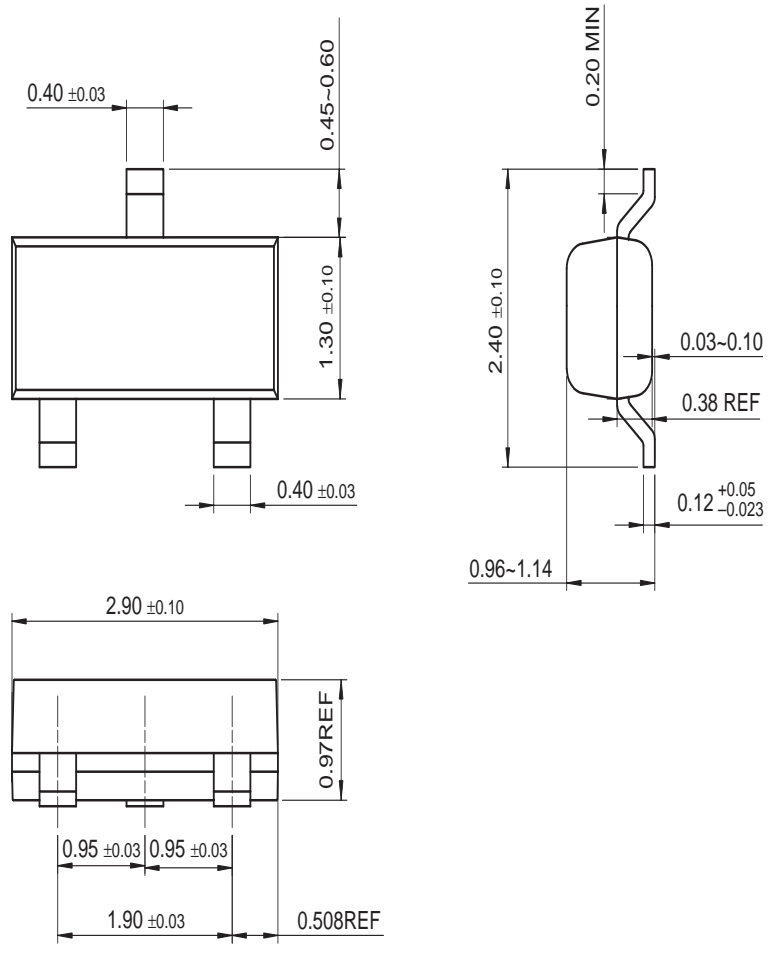


Figure 6. Power Dissipation vs Ambient Temperature



Mechanical Dimensions

SOT-23



Dimensions in Millimeters

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Build it Now™	FRFET™	MicroFET™	QS™	TinyLogic <sup>®</sup>
CoolFET™	GlobalOptoisolator™	MicroPak™	QT Optoelectronics™	TINYOPTO™
CROSSVOLT™	GTO™	MICROWIRE™	Quiet Series™	TruTranslation™
DOME™	HiSeC™	MSX™	RapidConfigure™	UHC™
EcoSPARK™	i <sup>2</sup> C™	MSXPro™	RapidConnect™	UltraFET <sup>®</sup>
E <sup>2</sup> CMOS™	i-Lo™	OCX™	μSerDes™	UniFET™
EnSigna™	ImpliedDisconnect™	OCXPro™	ScalarPump™	VCX™
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